

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	10015	isolation adj structure	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 15:58
S2	32	insulation adj structure and semiconductor and active adj area	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 15:59
S3	32	insulation adj structure and semiconductor and active adj area	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 15:59
S4	11	insulation adj structure and semiconductor and active adj area and memory adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:05
S5	351	isolation adj structure and semiconductor and active adj area and memory adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:03
S6	106	isolation adj structure and semiconductor and active adj area and memory adj cell and recess	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:13
S7	0	isolation adj structure and semiconductor and active adj area and memory adj cell and recess and resistor and capacitot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:13
S8	1	isolation adj structure and semiconductor and active adj area and memory adj cell and recess and resistor and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:14
S9	25	isolation adj structure and semiconductor and active adj area and memory adj cell and recess and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:15

S10	35	isolation adj structure and semiconductor and active adj area and memory adj cell and recess and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:41
S11	1386	(438/424).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 16:44
S12	89	S11 and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:42
S13	234	S11 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 16:42
S14	242	(438/425).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:06
S15	25	(438/499).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:06
S16	457	(257/499).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:54
S17	404	(257/528).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:54
S18	1263	(257/536).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:55
S19	1086	(257/506).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:55

S20	231	(257/509).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:55
S21	757	(257/510).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/04 17:55
S22	88	S21 and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 17:55
S23	165	S21 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/04 17:55
S24	47	S22 and S23	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 09:02
S25	757	(257/510).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/07 09:02
S26	88	S25 and resistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 09:02
S27	165	S25 and capacitor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 09:02
S28	2	S26 and S27 and projection	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/07 09:03